

DERWENT-ACC-NO: 2001-511244

DERWENT-WEEK: 200156

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TITLE: Sputtering target for semiconductor

INVENTOR: BAE, G H

PATENT-ASSIGNEE: HYUNDAI MICROELECTRONICS CO LTD [HYUNN]

PRIORITY-DATA: 1999KR-0032332 (August 6, 1999)

PATENT-FAMILY:

| PUB-NO | PUB-DATE | LANGUAGE |
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| PAGES MAIN-IPC | | |
| KR 2001017037 A | <u>March 5, 2001</u> | N/A |
| 001 H01L 021/20 | | |

APPLICATION-DATA:

| PUB-NO | APPL-DESCRIPTOR | APPL-NO |
|----------------|-----------------|----------------|
| APPL-DATE | | |
| KR2001017037A | N/A | 1999KR-0032332 |
| August 6, 1999 | | |

INT-CL (IPC): H01L021/20

ABSTRACTED-PUB-NO: KR2001017037A

BASIC-ABSTRACT:

NOVELTY - A sputtering target for a semiconductor is provided to remarkably reduce a foreign substance and to improve yield of a wafer, by rounding a corner of a portion necessary for sputtering.

DETAILED DESCRIPTION - A corner portion(10a) of a portion necessary for sputtering is processed to be round. A radius of curvature of the rounded portion is twice a radius of a sputtering target(10) used in evaporating an aluminum layer. When the corner of the target is round, a plasma region is reduced and plasma density becomes high. Plasma is lightly formed in the

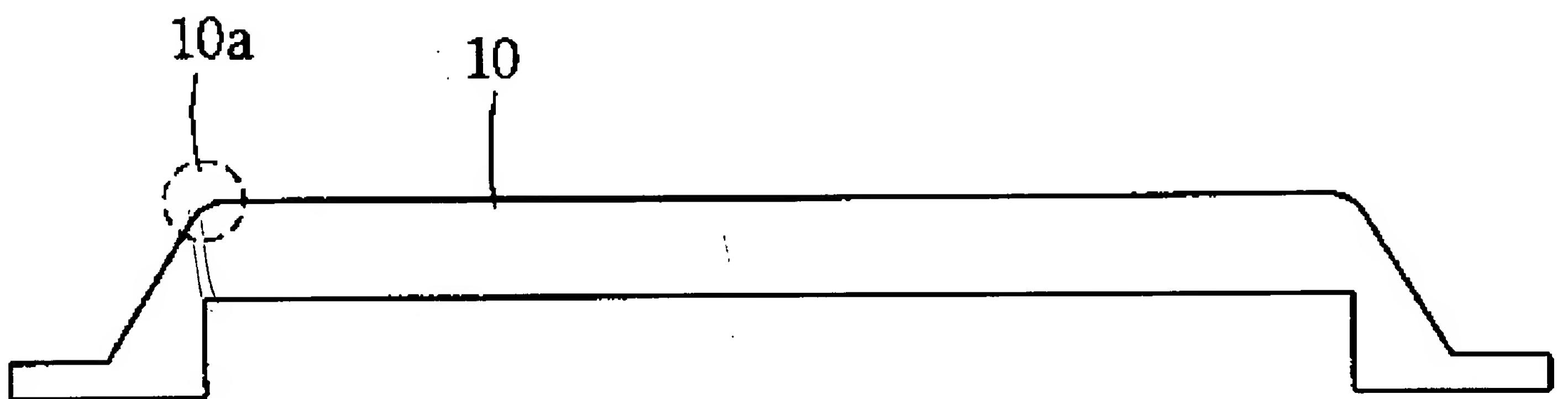
corner portion or in a front surface of the target so that a blackening phenomenon is reduced.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: **SPUTTER TARGET** SEMICONDUCTOR

DERWENT-CLASS: U11

EPI-CODES: U11-C01J1;



6"

6"

6"

